

Preliminary Amendment dated: 23 December 2004
Title: An Ion Implantation Device and a Method of Semiconductor Manufacturing ...
Applicants: Horsky et al.
Attorney Docket No.: 211843-00032

AMENDMENT TO THE SPECIFICATION

On page 1 please amend the “Cross Reference to Related Applications” as follows:

This application claims the benefit of and priority to PCT International Application No. PCT/US03/020197 filed on June 26, 2003, which, in turn, is a continuation-in-part to U.S. Provisional Application No. 60/463,965, filed on April 18, 2003, entitled “An Ion Implantation Device and a Method of Semiconductor Manufacturing by the Implantation of Boron Hydride Cluster Ions,” and U.S. Patent Application No. 10/183,768, filed on June 26, 2002, entitled “Electron Impact Ion Source.”